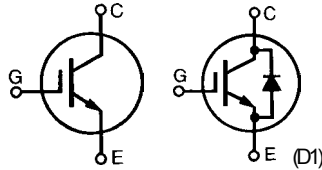


HiPerFAST™ IGBT

IXGH39N60B
IXGH39N60BD1
IXGT39N60B
IXGT39N60BD1

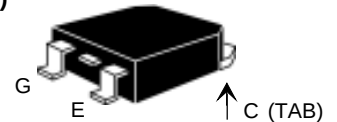
$V_{CES} = 600 \text{ V}$
 $I_{C25} = 76 \text{ A}$
 $V_{CE(sat)} = 1.7 \text{ V}$
 $t_{fi} = 200 \text{ ns}$

Preliminary data

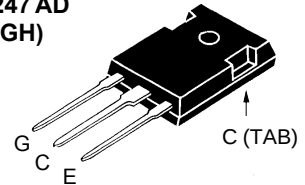


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	76	A
I_{C90}	$T_C = 90^\circ\text{C}$	39	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	152	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 22 \Omega$ Clamped inductive load	$I_{CM} = 76$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	200	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque (M3) TO-247	1.13/10Nm/lb.in.	
Weight		TO-247 AD	6 g
		TO-268	4 g

TO-268 (IXGT)



TO-247 AD (IXGH)



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard packages JEDEC TO-247 AD & TO-268
- High current handling capability
- Newest generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

Applications

- PFC circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

Advantages

- High power density
- Very fast switching speeds for high frequency applications

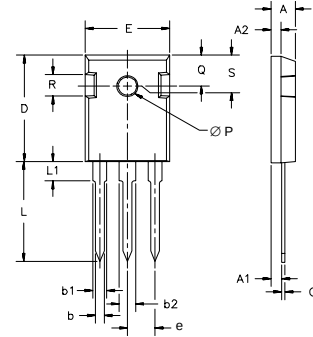
Symbol	Test Conditions		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
			Min.	Typ.	Max.
BV_{CES}	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	39N60B	600		V
	$I_C = 750 \mu\text{A}$	39N60BD1	600		
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	39N60B	2.5		5.0 V
	$I_C = 500 \mu\text{A}$	39N60BD1	2.5		5.0 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}, T_J = 25^\circ\text{C}$	39N60B			200 μA
	$V_{GE} = 0 \text{ V}, T_J = 125^\circ\text{C}$	39N60B			1 mA
	$T_J = 125^\circ\text{C}$	39N60BD1			3 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$				$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{90}, V_{GE} = 15 \text{ V}$				1.7 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}; V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	19	28	S
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	2750		pF
C_{oes}		39N60B 200		pF
C_{res}		39N60BD1 240		pF
		50		pF
Q_G	$I_C = I_{C90}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$	110	150	nC
Q_{GE}		25	35	nC
Q_{GC}		40	75	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 4.7\text{ }\Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G	25		ns
t_{ri}		30		ns
$t_{d(off)}$		250	500	ns
t_{fi}		200	360	ns
E_{off}		4.0	6.0	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}$ $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 4.7\text{ }\Omega$ Remarks: Switching times may increase for V_{CE} (Clamp) $> 0.8 \cdot V_{CES}$, higher T_J or increased R_G	25		ns
t_{ri}		30		ns
E_{on}		0.3		mJ
$t_{d(off)}$		360		ns
t_{fi}		350		ns
E_{off}		6.0		mJ
R_{thJC}			0.62	K/W
R_{thCK}		0.25		K/W

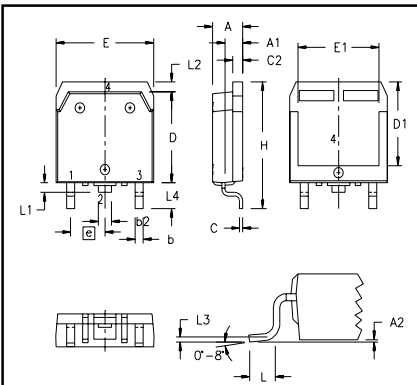
Reverse Diode (FRED) **Characteristic Values**
($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Test Conditions	min.	typ.	max.
V_F	$I_F = I_{C90}, V_{GE} = 0\text{ V}$, Pulse test $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$	$T_J = 150^\circ\text{C}$		1.6 V
		$T_J = 25^\circ\text{C}$		2.5 V
I_{RM}	$I_F = I_{C90}, V_{GE} = 0\text{ V}, -di_F/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$ $I_F = 1\text{ A}; -di/dt = 100\text{ A}/\mu\text{s}; V_R = 30\text{ V}$	6		A
t_{rr}		$T_J = 100^\circ\text{C}$ 100		ns
		$T_J = 25^\circ\text{C}$ 25		ns
R_{thJC}			0.9	K/W

TO-247 AD Outline



Dim.	Millimeter	Inches
	Min.	Max.
A	4.7	5.3
A1	2.2	2.54
A2	2.2	2.6
b	1.0	1.4
b1	1.65	2.13
b2	2.87	3.12
C	.4	.8
D	20.80	21.46
E	15.75	16.26
e	5.20	5.72
L	19.81	20.32
L1		4.50
ØP	3.55	3.65
Q	5.89	6.40
R	4.32	5.49
S	6.15	BSC



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e		.215 BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

Fig. 1. Saturation Voltage Characteristics @ 25 Deg. C

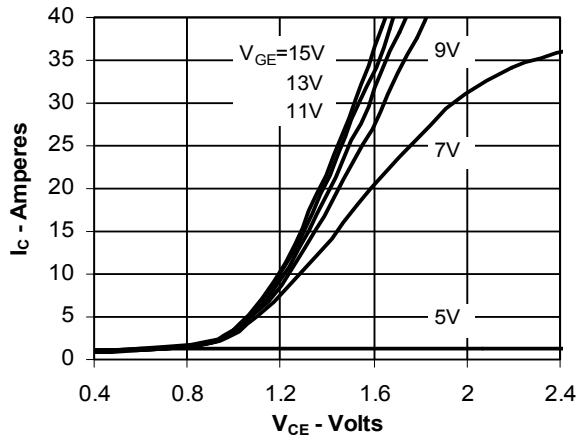


Fig. 2. Extended Output Characteristics @ 25 Deg. C

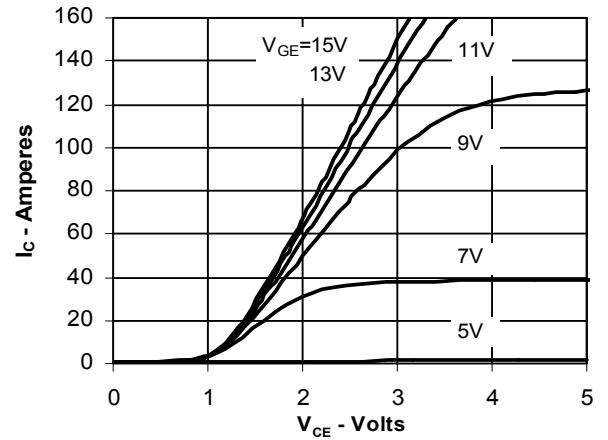


Fig. 3. Saturation Voltage Characteristics @ 125 Deg. C

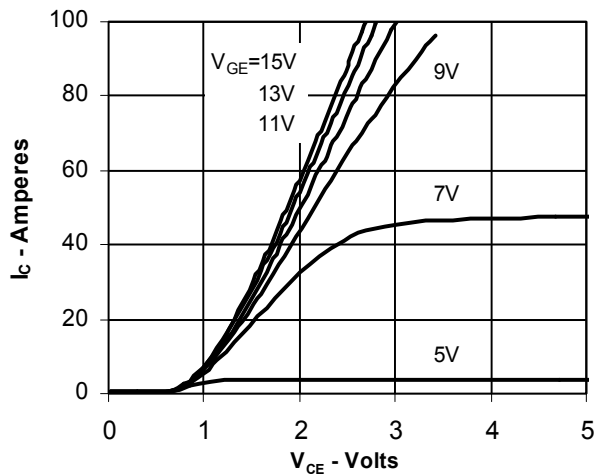


Fig. 4. Temperature Dependence of $V_{CE(SAT)}$

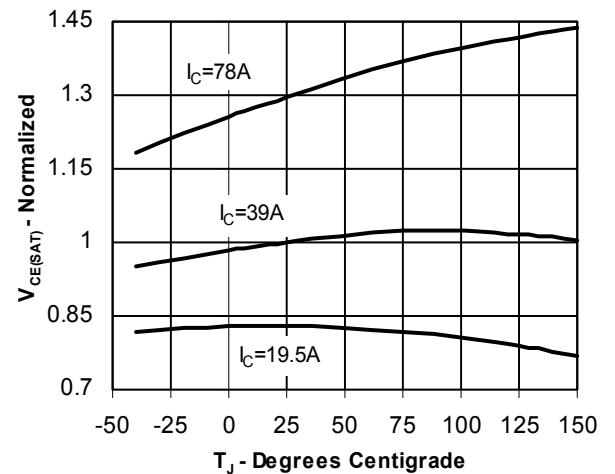


Fig. 5. BV_{CES} & $V_{GE(TH)}$ vs. Junction Temperature

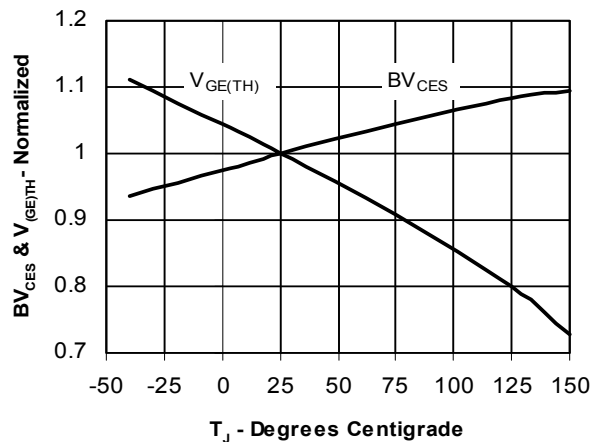


Fig. 6. Admittance

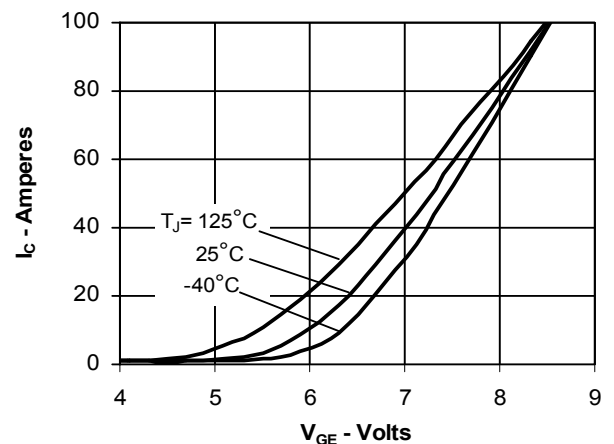


Fig. 7. Transconductance

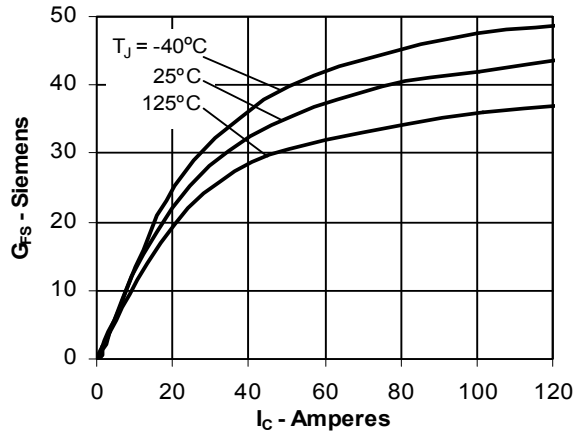


Fig. 8. Dependence of E_{OFF} on I_c

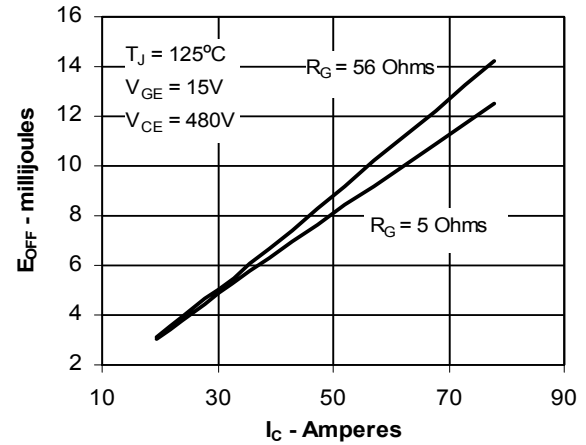


Fig. 9. Dependence of E_{OFF} on R_G

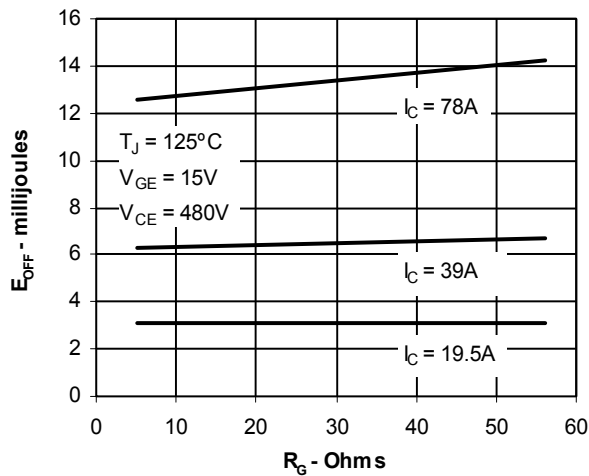


Fig. 10. Dependence of E_{OFF} on Temperature

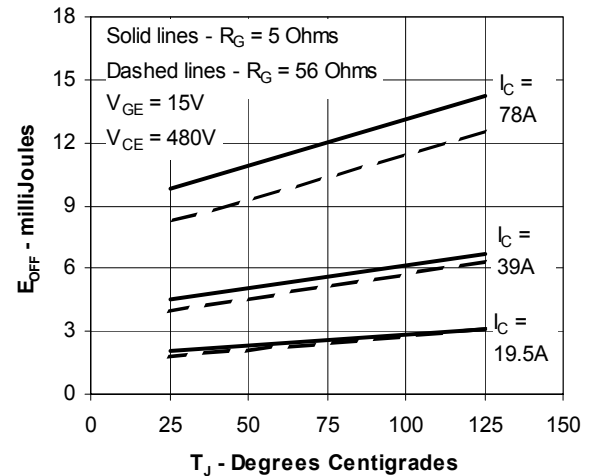


Fig. 11. Gate Charge

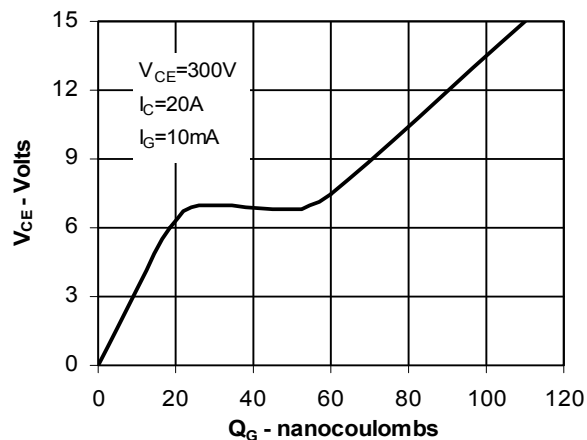
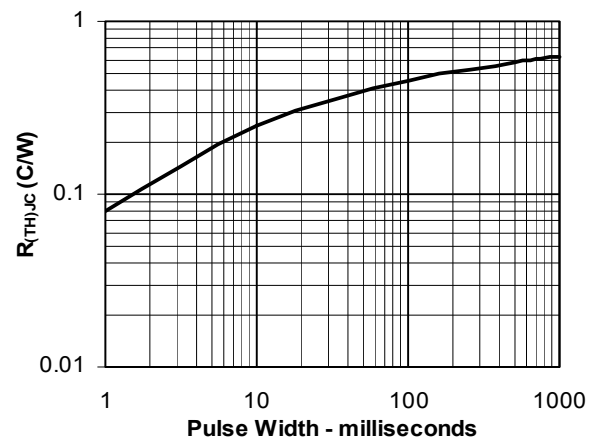


Fig. 12. Transient Thermal Response



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	

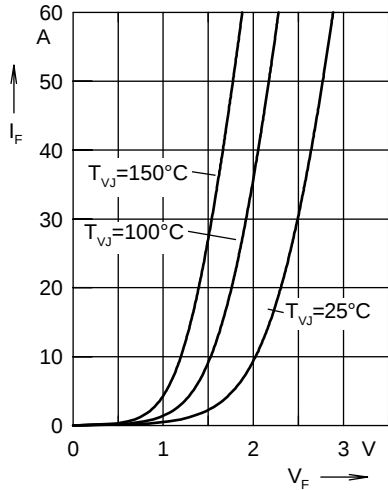


Fig. 12 Forward current I_F versus V_F

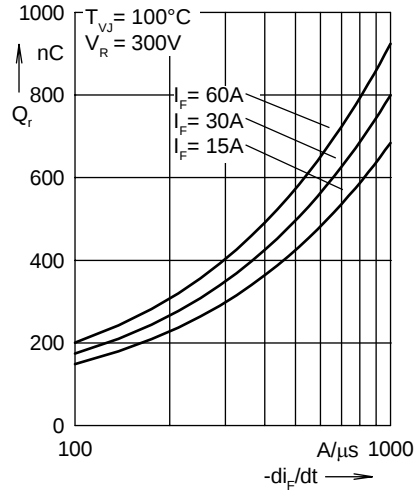


Fig. 13 Reverse recovery charge Q_r versus $-di_F/dt$

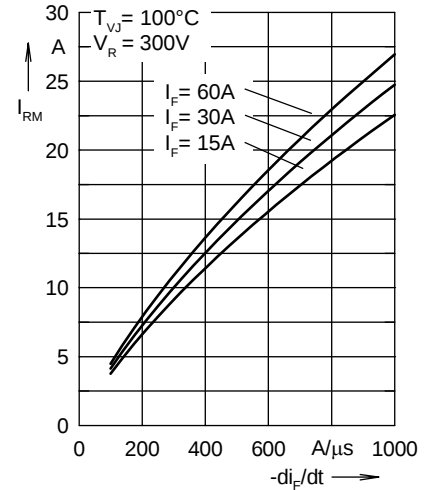


Fig. 14 Peak reverse current I_{RM} versus $-di_F/dt$

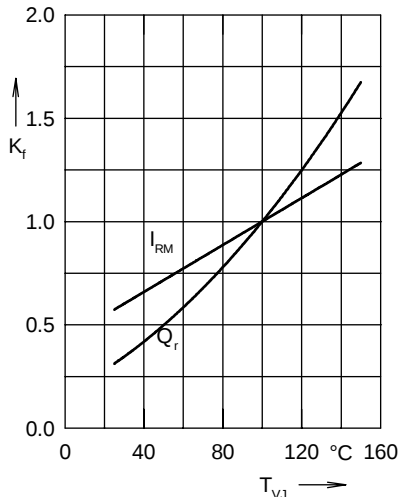


Fig. 15 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

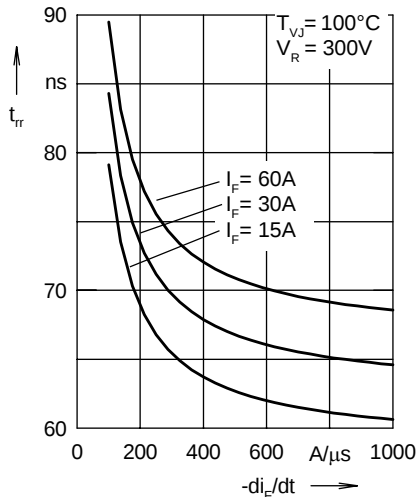


Fig. 16 Recovery time t_{rr} versus $-di_F/dt$

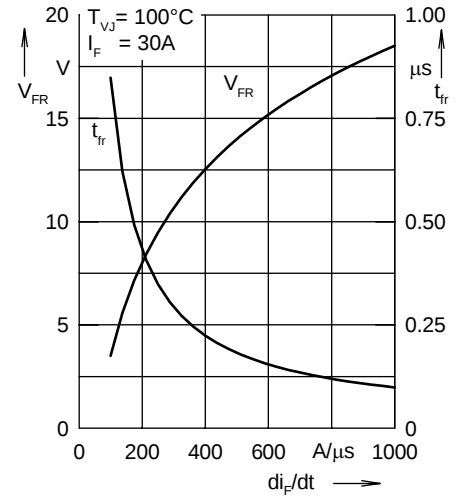


Fig. 17 Peak forward voltage V_{FR} and t_{rr} versus di_F/dt

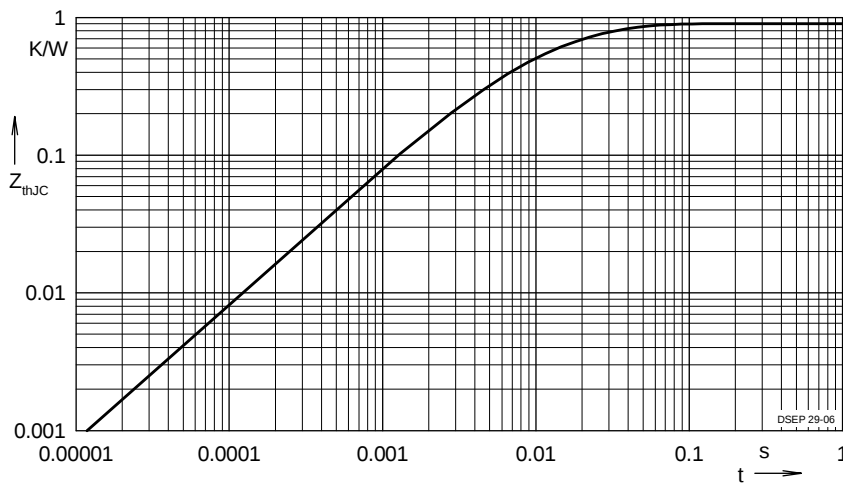


Fig. 18 Transient thermal resistance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.502	0.0052
2	0.193	0.0003
3	0.205	0.0162